



DMP3021SFVWQ

30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	Rds(on) Max	I⊳ Max Tc = +25°C		
-30V	15mΩ @ V _{GS} = -10V	-42A		
	25mΩ @ V _{GS} = -5V	-32A		

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

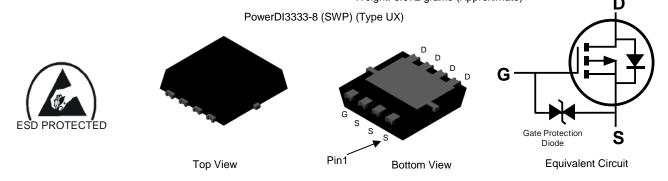
Features and Benefits

- Low R_{DS(ON)} ensures on-state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP3021SFVWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/guality/product-definitions/

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3) Weight: 0.072 grams (Approximate)



Ordering Information (Note 4)

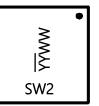
Part Number	Case	Packaging
DMP3021SFVWQ-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel
DMP3021SFVWQ-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\frac{SW2}{YY} = Product Type Marking Code$ $\frac{YY}{YY} WW = Date Code Marking$ $\frac{YY}{YY} = Last Two Digits of Year (ex: 21 = 2021)$ WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			VDSS	-30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 6) VGs = -10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	lo	-11 -9	A
Continuous Drain Current (Note 7) V_{GS} = -10V	Steady State	Tc = +25°C Tc = +70°C	lo	-42 -34	А
Maximum Continuous Body Diode Forward Current (Note 7)			ls	-42	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			ldм	-128	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	-128	A
Avalanche Current (Note 8) L = 1mH			las	-13	A
Avalanche Energy (Note 8) L = 1mH			Eas	84	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	126.6	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	51.2	°C/W
Thermal Resistance, Junction to Case (Note 7)	R _{0JC}	3.6	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30			V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS			-1	μA	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	lgss			±10	μA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	Vgs(th)	-1.0	_	-2.5	V	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	
Static Drain-Source On-Resistance	Descer		10.3	15	mΩ	$V_{GS} = -10V, I_D = -8A$	
	RDS(ON)	—	15.5	25		$V_{GS} = -5V, I_{D} = -5A$	
Diode Forward Voltage	Vsd	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss		1799	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	—	259		pF		
Reverse Transfer Capacitance	Crss	—	225	—	pF		
Gate Resistance	Rg	—	2.1	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$	
Total Gate Charge (V _{GS} = -5V)	Qg		17.4	—	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	34	_	nC		
Gate-Source Charge	Qgs	_	5.1	_	nC	$V_{DS} = -15V, I_D = -10A$	
Gate-Drain Charge	Q _{gd}	_	8.4	_	nC	7	
Turn-On Delay Time	t _{D(ON)}	_	6.5	_	ns		
Turn-On Rise Time	tR		18.3		ns	$V_{DD} = -15V, V_{GS} = -10V,$ $R_G = 3\Omega, I_D = -10A$	
Turn-Off Delay Time	tD(OFF)	_	35.8	_	ns		
Turn-Off Fall Time	tF	_	23.7		ns		
Reverse Recovery Time	trr	_	14.9		ns		
Reverse Recovery Charge	QRR		15	—	nC	Is = -8A, dI/dt = 500A/μs	

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

Device mounted on FR-4 substrate PC board, 20z copper, with thermal bias to bottom layer 1-inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).

8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.

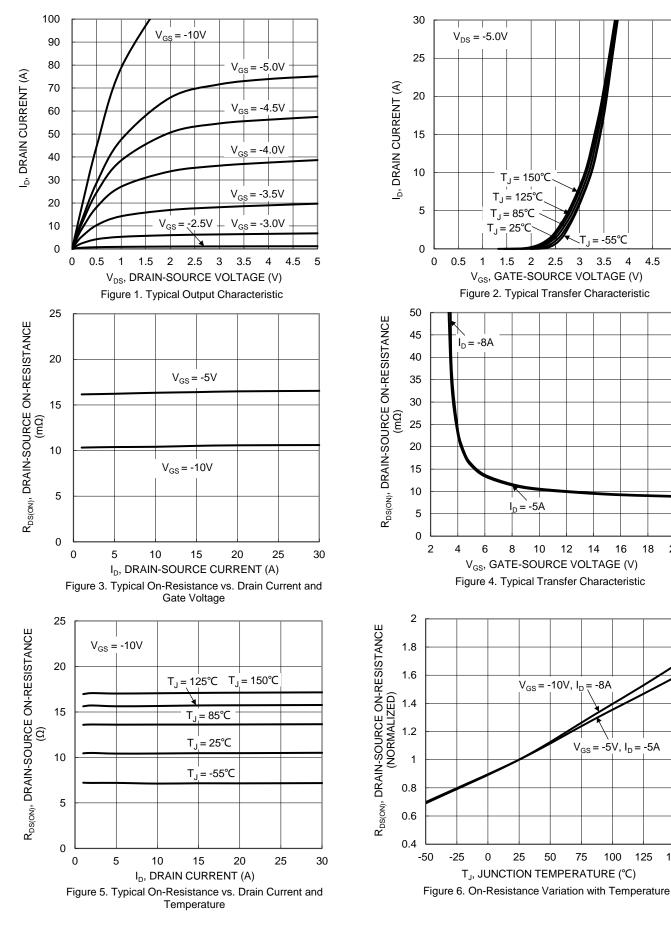


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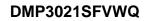
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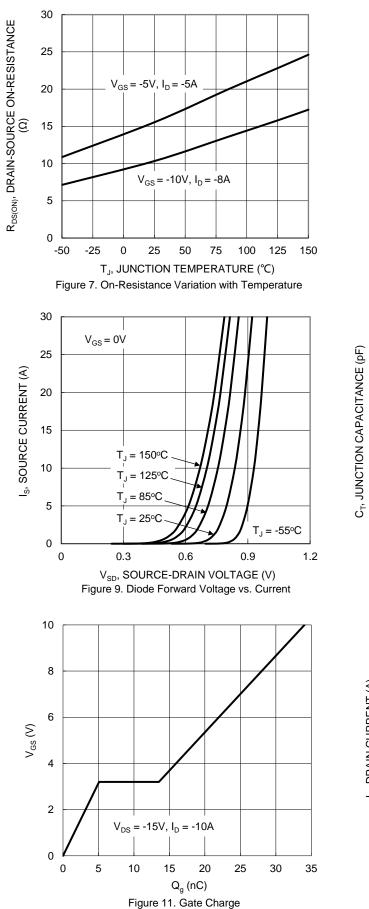
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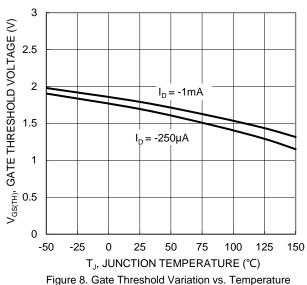


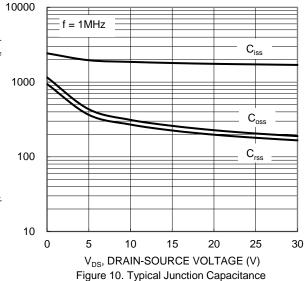
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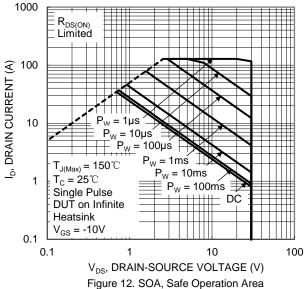




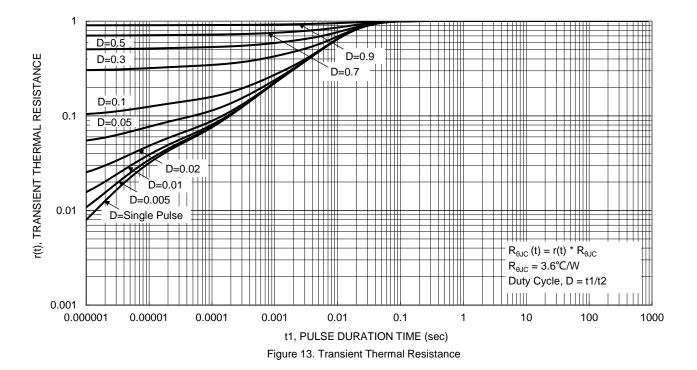








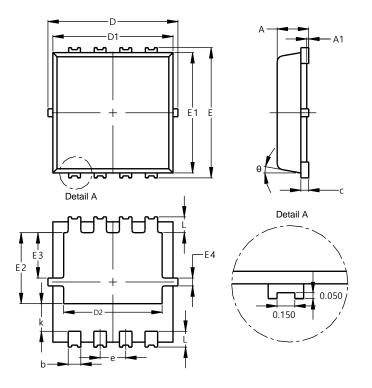






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



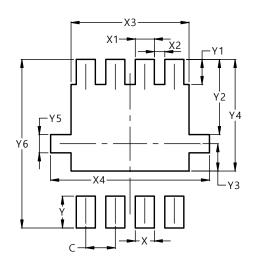
PowerDI3333-8 (SWP) (Type UX)

PowerDI3333-8 (SWP)						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
E	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700



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